

## Silicon NPN Power Transistors

BD941

## DESCRIPTION

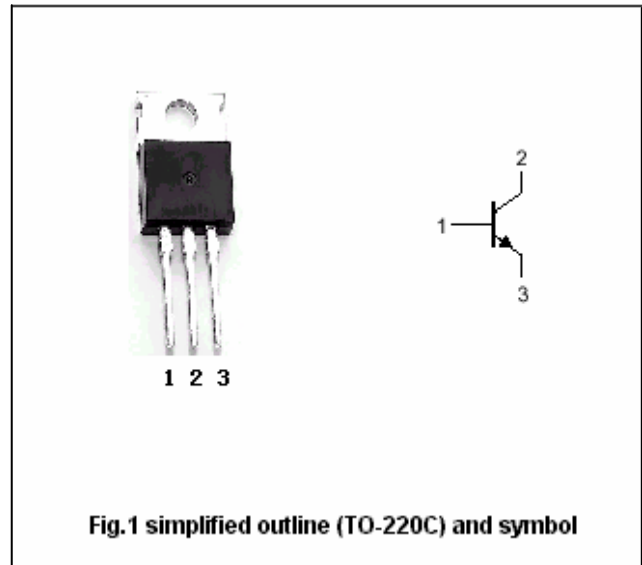
- With TO-220C package
- Low collector saturation voltage

## APPLICATIONS

- For power switching applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a=25$  )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	140	V
$V_{CEO}$	Collector-emitter voltage	Open base	140	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		3	A
$I_{CM}$	Collector current-Peak		6	A
$P_C$	Collector dissipation	$T_C=25$	30	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-50~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	140			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.2A			0.7	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =140V; I <sub>E</sub> =0			50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.2A ; V <sub>CE</sub> =4V	40		250	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =4V	15			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.25A ; V <sub>CE</sub> =10V	3			MHz

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PACKAGE OUTLINE

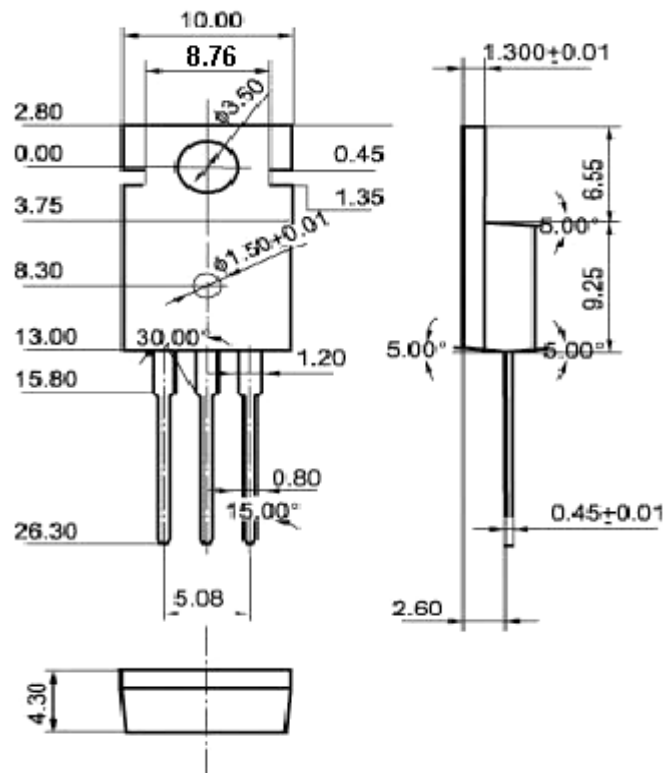


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10mm)